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(54) **Title:** METHOD FOR REMOVING ETCHING RESIDUES FROM SEMICONDUCTOR COMPONENTS

(57) **Abstract:** A method for cleaning structured surfaces of semiconductor components to remove photoresist and etching residues after the etching of the surface, comprising: a) treatment of the surface with an acidic aqueous solution comprising one or more acids and one or more oxidizing agents, b) removal of the photoresist and c) washing with demineralized water in the stated sequence.